FET DROs at V-Band

W. Yau, E.T. Watkins and Y.C. Shih. "FET DROs at V-Band." 1991 MTT-S International Microwave Symposium Digest 91.1 (1991 Vol. I [MWSYM]): 281-284.

MESFET DROs have been demonstrated at V-band. The first unit operates at 51.2 GHz with an output power as high as 9 dBm. The second unit operates at 65.6 GHz with an output power of 7.6 dBm. Dc to RF efficiencies were 18 percent and 14 percent, respectively. Power variation is less than ±0.25 dB over a temperature from 0 to 50° C. The high output power associated with the dc-to-RF efficiency is believed to be the highest ever reported.

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